CPH3123-TL-E Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	CPH3123-TL-E-DG
Manufacturer	onsemi
Manufacturer Product Number	CPH3123-TL-E
Description	TRANS PNP 50V 3A 3CPH
Detailed Description	Bipolar (BJT) Transistor PNP 50 V 3 A 390MHz 900 m W Surface Mount 3-CPH

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
CPH3123-TL-E	onsemi
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	3 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
50 V	650mV @ 100mA, 2A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
1µA (ICBO)	200 @ 100mA, 2V
Power - Max:	Frequency - Transition:
900 mW	390MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
SC-96	3-CPH
Base Product Number:	
CPH3123	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	

Ordering number : EN7221B

CPH3123/CPH3223

Bipolar Transistor
(−)50V, (−)3A, Low V_{CE}(sat), (PNP)NPN Single CPH3

ON Semiconductor®
http://onsemi.com

Applications

- DC-DC converters, relay drivers, lamp drivers, motor drivers, flash

Features

- Adoption of MBIT processes
- Large current capacity
- Low collector-to-emitter saturation voltage
- High-speed switching
- Ultrasmall package facilitates miniaturization in end products (mounting height : 0.9mm)
- High allowable power dissipation

Specifications ( ): CPH3123

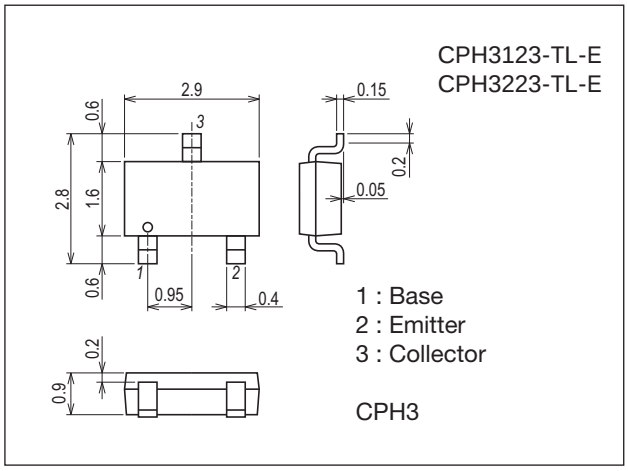
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(−50)100	V
Collector-to-Emitter Voltage	V_{CES}		(−50)100	V
Collector-to-Emitter Voltage	V_{CEO}		(−)50	V
Emitter-to-Base Voltage	V_{EBO}		(−)6	V
Collector Current	I_C		(−)3	A
Collector Current (Pulse)	I_{CP}		(−)6	A
Base Current	I_B		(−)600	mA
Collector Dissipation	P_C	When mounted on ceramic substrate (600mm^2×0.8mm)	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

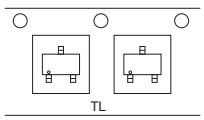
unit : mm (typ)
7015A-003



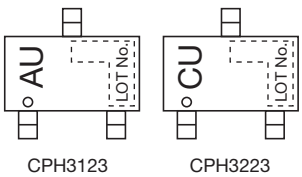
Product & Package Information

- Package : CPH3
- JEITA, JEDEC : SC-59, TO-236, SOT-23
- Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL



Marking



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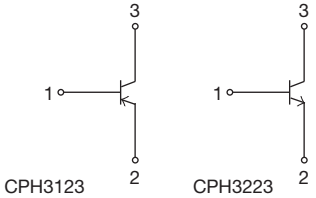
Electrical Connection



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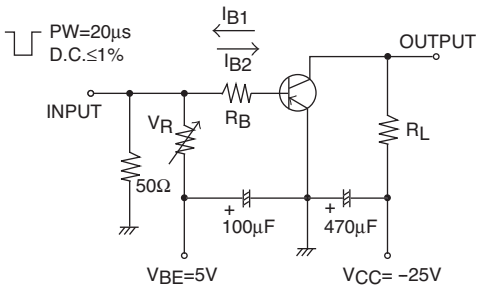
Electrical Characteristics at Ta=25°C

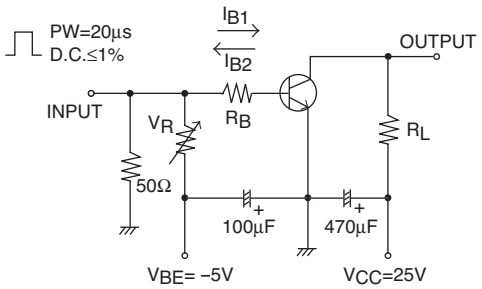
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	V_{CB}=(−)40V, I_E=0A			(−)1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=(−)4V, I_C=0A			(−)1	μA
DC Current Gain	h_{FE}	V_{CE}=(−)2V, I_C=(−)100mA	200		560	
Gain-Bandwidth Product	f_T	V_{CE}=(−)10V, I_C=(−)500mA		(390)380		MHz
Output Capacitance	Cob	V_{CB}=(−)10V, f=1MHz		(24)13		pF
Collector-to-Emitter Saturation Voltage	V_{CE}(sat)1	I_C=(−)1A, I_B=(−)50mA		(−115)90	(−230)130	mV
	V_{CE}(sat)2	I_C=(−)2A, I_B=(−)100mA		(−240)160	(−650)240	mV
Base-to-Emitter Saturation Voltage	V_{BE}(sat)	I_C=(−)2A, I_B=(−)100mA		(−)0.88	(−)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=(−)10μA, I_E=0A	(−50)100			V
Collector-to-Base Breakdown Voltage	$V_{(BR)CES}$	I_C=(−)100μA,R_{BE}=0Ω	(−50)100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=(−)1mA, R_{BE}=∞	(−)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=(−)10μA, I_C=0A	(−)6			V
Turn-On Time	t_{on}	See specified Test Circuit.		(30)35		ns
Storage Time	t_{stg}			(230)300		ns
Fall Time	t_f			(18)25		ns

Switching Time Test Circuit



I_C= −10I_{B1}=10I_{B2}= −1A

CPH3123

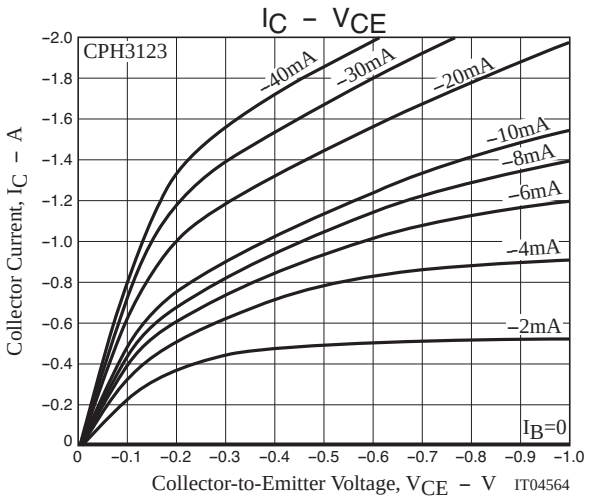


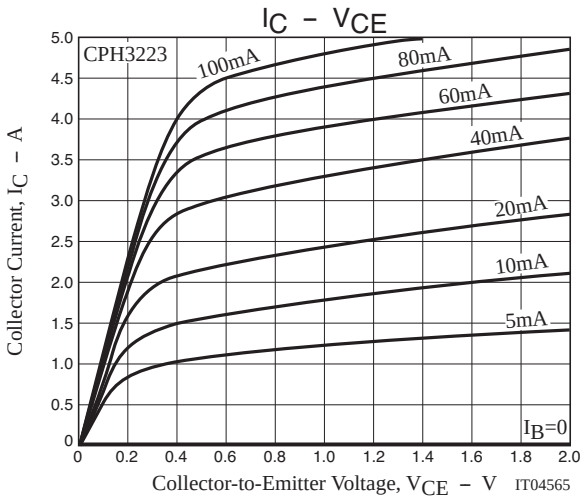
I_C=10I_{B1}= −10I_{B2}=1A

CPH3223

Ordering Information

Device	Package	Shipping	memo
CPH3123-TL-E	CPH3	3,000pcs./reel	Pb Free
CPH3223-TL-E	CPH3	3,000pcs./reel	Pb Free





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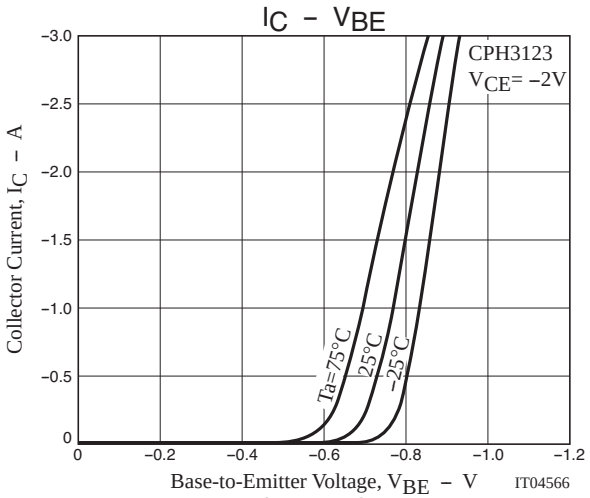

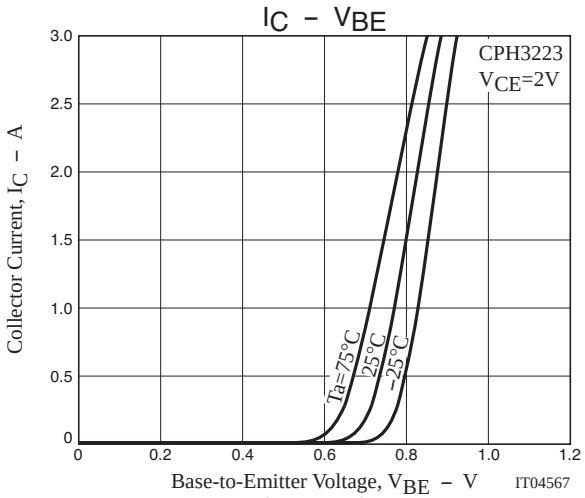

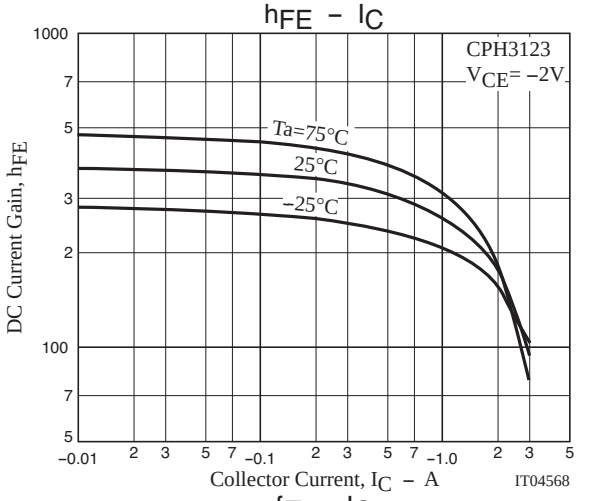

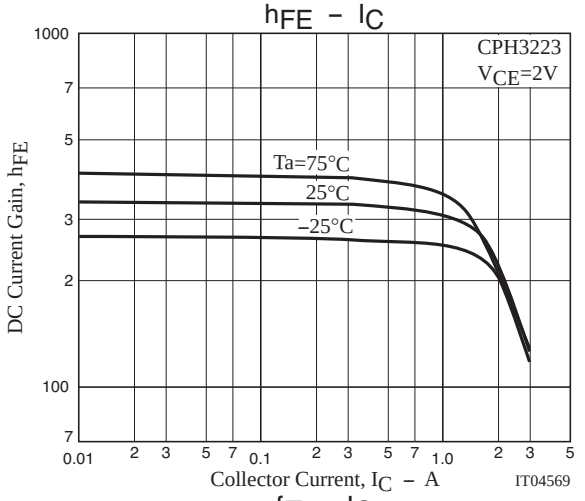

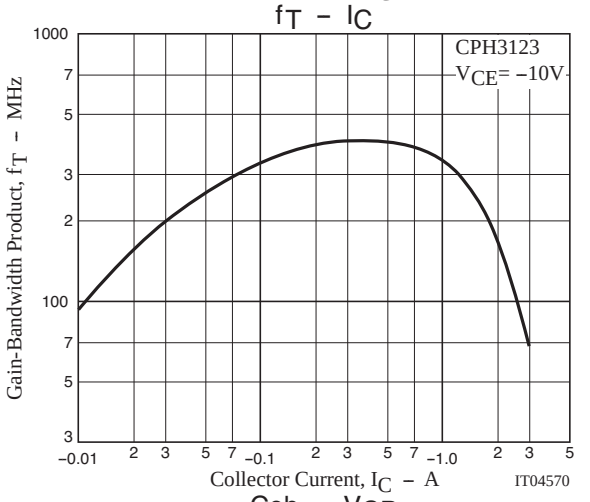

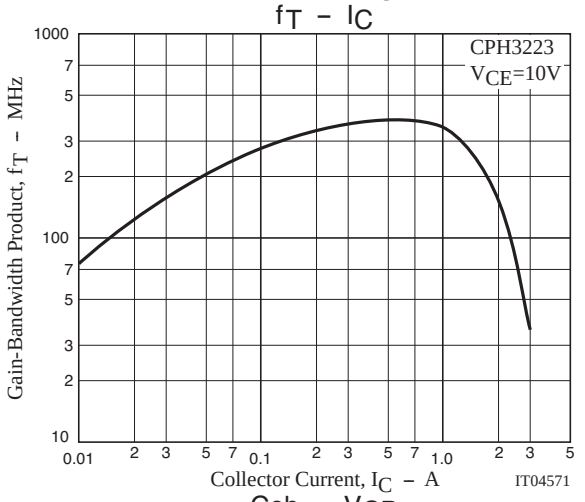

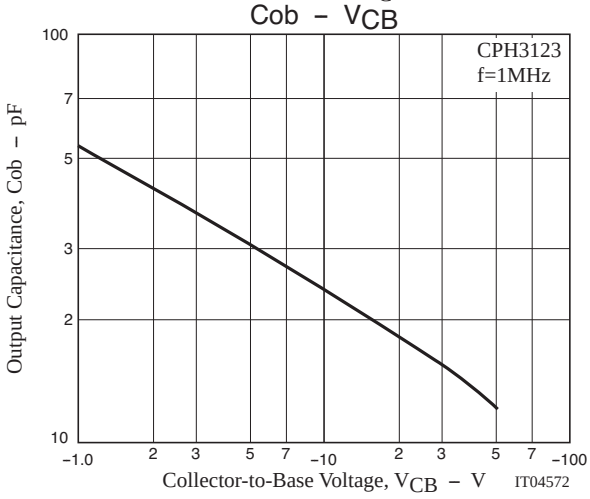

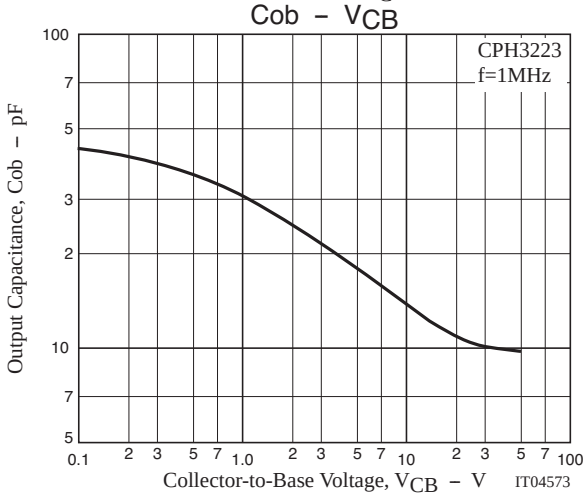

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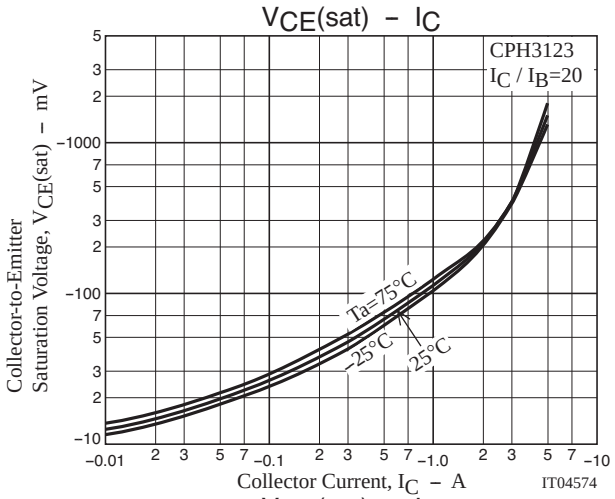
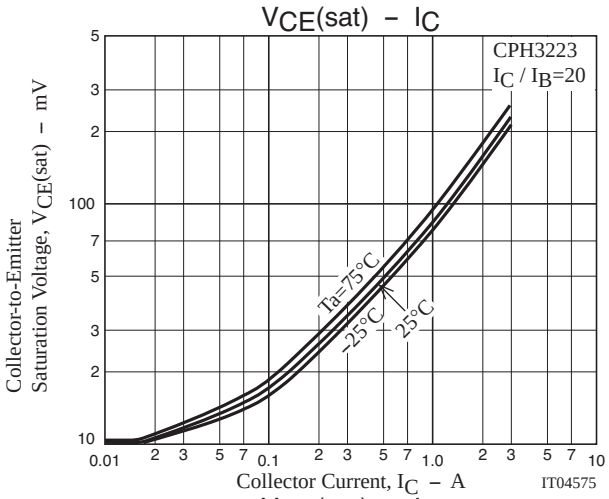
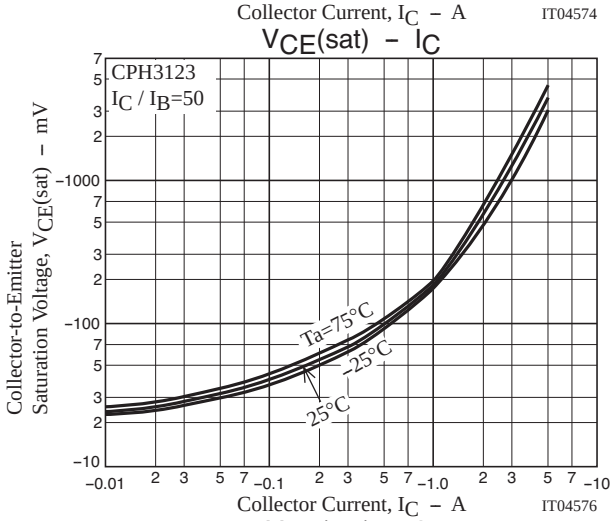
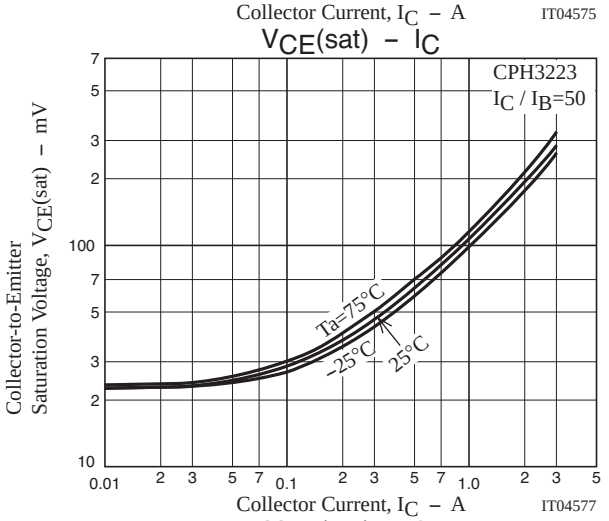
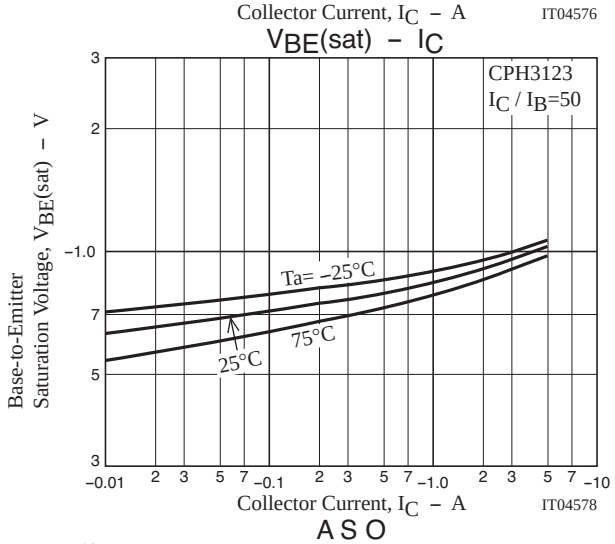
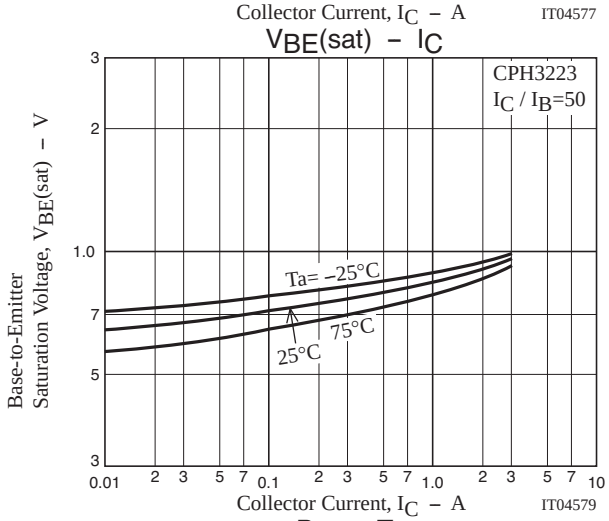


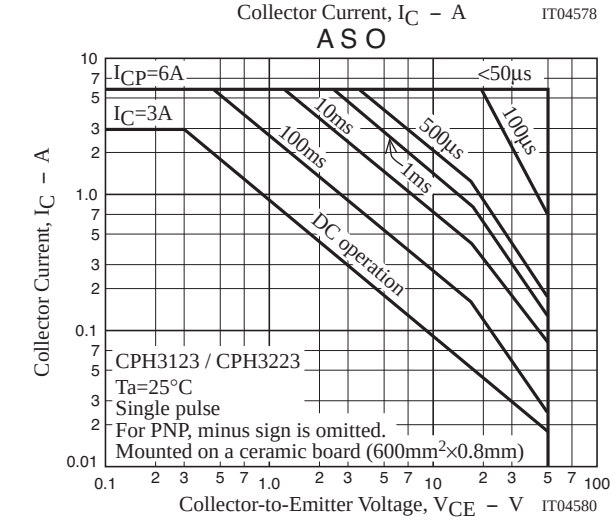


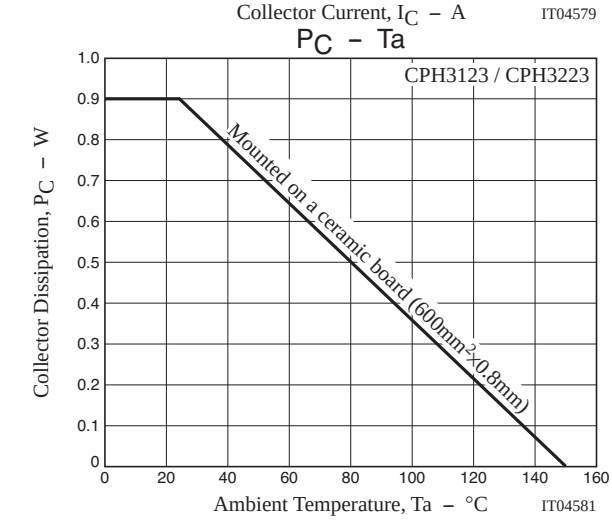












CPH3123/CPH3223

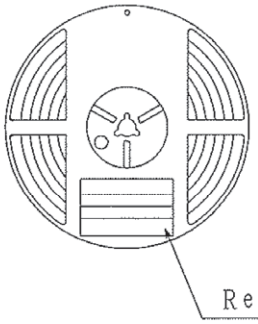
Embossed Taping Specification

CPH3123-TL-E, CPH3223-TL-E

1. Packing Format

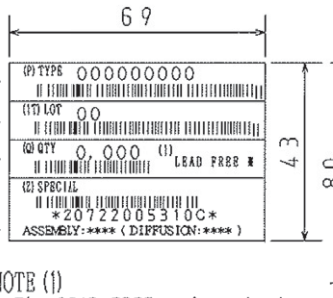
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CPH3	CPH3	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Packing method



Reel label

Reel label, Inner box label (unit:mm)



Type No.

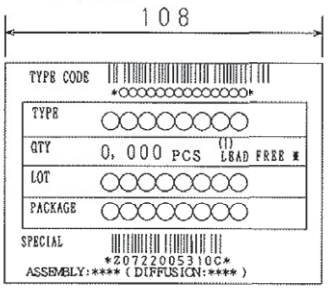
LOT No.

Quantity

Origin

Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.

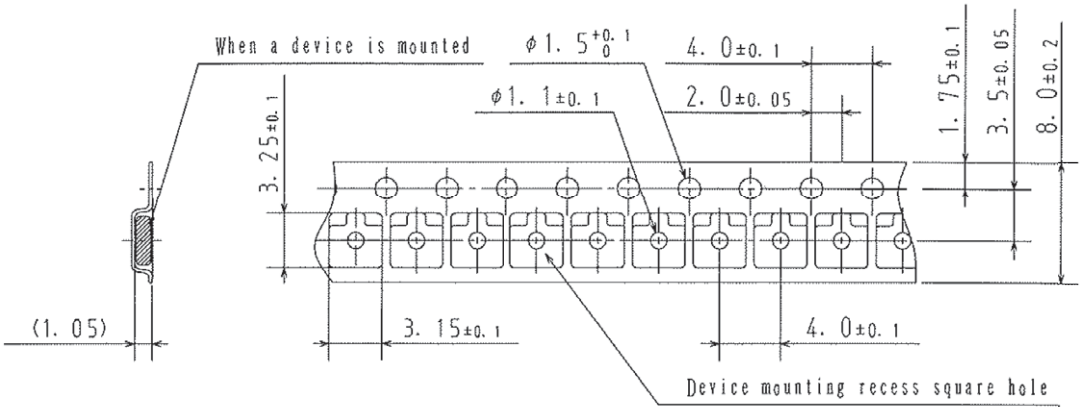


NOTE (1)
The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

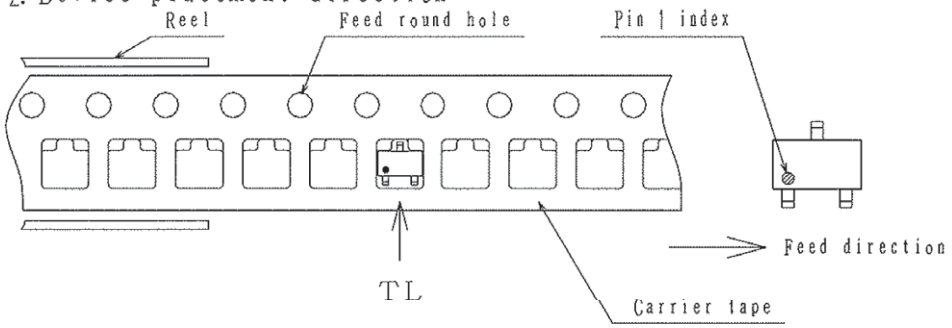
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction



Those with one electrode terminal on the feed hole side·····TL

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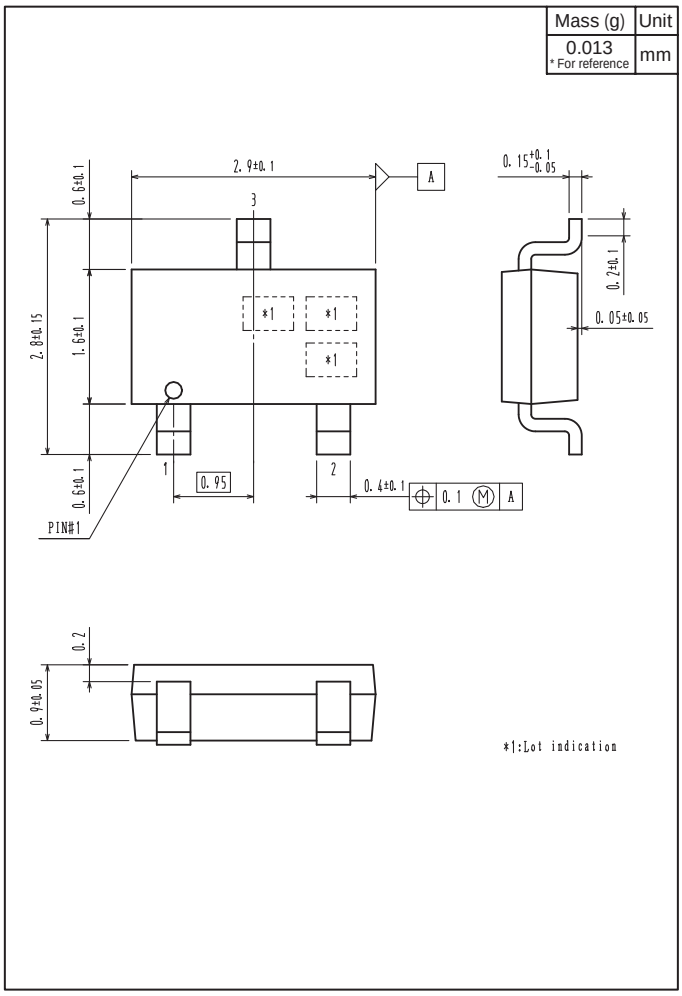
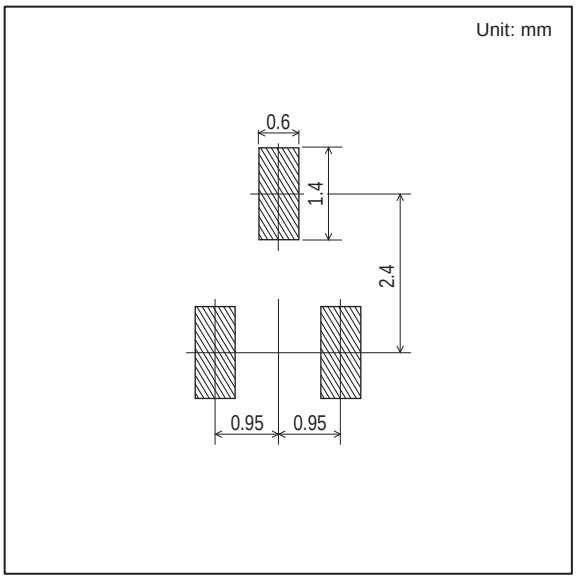
Outline Drawing

CPH3123-TL-E, CPH3223-TL-E



Land Pattern Example



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